

# Olga SÃ¡nchez

## List of Publications by Year in descending order

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65  
papers

1,009  
citations

430874

18  
h-index

477307

29  
g-index

65  
all docs

65  
docs citations

65  
times ranked

1146  
citing authors

#	ARTICLE	IF	CITATIONS
1	ZnOTe Compounds Grown by DC-Magnetron Co-Sputtering. Coatings, 2021, 11, 570.	2.6	1
2	Special Issue "1D, 2D, and 3D ZnO: Synthesis, Characterization, and Applications" Coatings, 2021, 11, 696.	2.6	2
3	Effect of the Incorporation of Titanium on the Optical Properties of ZnO Thin Films: From Doping to Mixed Oxide Formation. Coatings, 2019, 9, 180.	2.6	9
4	ZnO <sub>1-x</sub> Te <sub>x</sub> thin films deposited by reactive magnetron co-sputtering: composition, structure and optical properties. MRS Advances, 2017, 2, 3111-3116.	0.9	2
5	Compositional and structural properties of nanostructured ZnO thin films grown by oblique angle reactive sputtering deposition: effect on the refractive index. Journal Physics D: Applied Physics, 2013, 46, 045306.	2.8	23
6	Continuous and Nanostructured TiO <sub>2</sub> Films Grown by dc Sputtering Magnetron. Journal of Nanoscience and Nanotechnology, 2012, 12, 9148-9155.	0.9	6
7	Influence of the oxygen partial pressure and post-deposition annealing on the structure and optical properties of ZnO films grown by dc magnetron sputtering at room temperature. Journal Physics D: Applied Physics, 2012, 45, 025303.	2.8	47
8	Coordination chemistry of titanium and zinc in Ti(1-x)Zn <sub>2x</sub> O <sub>2</sub> (0 ≤ x ≤ 1) ultrathin films grown by DC reactive magnetron sputtering. RSC Advances, 2012, 2, 2696.	3.6	13
9	In-depth multi-technique characterization of chromium-silicon mixed oxides produced by reactive ion beam mixing of the Cr/Si interface. Journal of Analytical Atomic Spectrometry, 2012, 27, 390.	3.0	6
10	Improving the visible transmittance of low-e titanium nitride based coatings for solar thermal applications. Applied Surface Science, 2011, 258, 1784-1788.	6.1	28
11	An XPS and ellipsometry study of Cr-Al mixed oxides grown by reactive magnetron sputtering. Surface and Coatings Technology, 2011, 206, 1484-1489.	4.8	17
12	Control of the optical properties of silicon and chromium mixed oxides deposited by reactive magnetron sputtering. Thin Solid Films, 2011, 519, 3509-3515.	1.8	7
13	Influence of aluminium incorporation on the structure of ZrN films deposited at low temperatures. Journal Physics D: Applied Physics, 2010, 43, 209801-209801.	2.8	0
14	Correlation between structure and optical properties in low emissivity coatings for solar thermal collectors. Thin Solid Films, 2010, 518, 5720-5723.	1.8	29
15	Influence of the aluminum incorporation on the structure of sputtered ZrN <sub>x</sub> films deposited at low temperatures. Vacuum, 2009, 83, 1236-1239.	3.5	8
16	Ti <sub>x</sub> Si <sub>y</sub> N nanocomposites by cathodic arc plasma deposition. Vacuum, 2009, 83, 1233-1235.	3.5	5
17	Influence of aluminium incorporation on the structure of ZrN films deposited at low temperatures. Journal Physics D: Applied Physics, 2009, 42, 115422.	2.8	6
18	Titanium nitride stamps replicating nanoporous anodic alumina films. Nanotechnology, 2007, 18, 165302.	2.6	8

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19	Hardness and tribology measurements on ZrN coatings deposited by reactive sputtering technique. <i>Vacuum</i> , 2007, 81, 1462-1465.	3.5	33
20	Wear resistance of titanium–aluminium–chromium–nitride nanocomposite thin films. <i>Vacuum</i> , 2007, 81, 1453-1456.	3.5	23
21	Corrosion behaviour of AlN and TiAlN coatings on iron. <i>Surface and Interface Analysis</i> , 2006, 38, 243-247.	1.8	6
22	Growth of CrNx films by DC reactive magnetron sputtering at constant N2/Ar gas flow. <i>Surface and Coatings Technology</i> , 2006, 200, 6047-6053.	4.8	60
23	Functional nanostructured titanium nitride films obtained by sputtering magnetron. <i>Thin Solid Films</i> , 2006, 495, 149-153.	1.8	16
24	Preparation and properties of novel magnetic composite nanostructures: Arrays of nanowires in porous membranes. <i>Physica B: Condensed Matter</i> , 2006, 384, 36-40.	2.7	15
25	Intrinsic anomalous surface roughening of TiN films deposited by reactive sputtering. <i>Physical Review B</i> , 2006, 73, .	3.2	54
26	Chemical stability of TiN, TiAlN and AlN layers in aggressive SO2 environments. <i>Surface and Interface Analysis</i> , 2005, 37, 1082-1091.	1.8	58
27	Molding and Replication of Ceramic Surfaces with Nanoscale Resolution. <i>Small</i> , 2005, 1, 300-309.	10.0	27
28	Growth dynamics of reactive-sputtering-deposited AlN films. <i>Journal of Applied Physics</i> , 2005, 97, 123528.	2.5	35
29	Structure and morphology evolution of AlN films grown by DC sputtering. <i>Surface and Coatings Technology</i> , 2004, 180-181, 140-144.	4.8	44
30	TiN/AlN bilayers and multilayers grown by magnetron co-sputtering. <i>Thin Solid Films</i> , 2003, 433, 211-216.	1.8	13
31	Deposition of TiN/AlN bilayers on a rotating substrate by reactive sputtering. <i>Surface and Coatings Technology</i> , 2002, 157, 26-33.	4.8	32
32	Synthesis and characterization of porous silica thin films deposited from MCM-41 evaporation. <i>Thin Solid Films</i> , 2002, 402, 111-116.	1.8	3
33	Hydrothermal growth of CdS and ZnS Nanoparticles in MOR-type zeolites. <i>Materials Science and Engineering C</i> , 2001, 15, 101-104.	7.3	21
34	Model of the bias-enhanced nucleation of diamond on silicon based on atomic force microscopy and x-ray-absorption studies. <i>Physical Review B</i> , 2000, 61, 10383-10387.	3.2	16
35	CdS doped-MOR type zeolite characterization. <i>Solid-State Electronics</i> , 1999, 43, 1171-1175.	1.4	15
36	Effect of the substrate temperature on the deposition of hydrogenated amorphous carbon by PACVD at 35 kHz. <i>Thin Solid Films</i> , 1999, 338, 88-92.	1.8	32

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37	SiOxNy Films deposited with SiCl <sub>4</sub> by remote plasma enhanced CVD. Journal of Materials Science, 1999, 34, 3007-3012.	3.7	5
38	Diamond nuclei formation in a microwave plasma assisted chemical vapor deposition (MWCVD) system. European Physical Journal Special Topics, 1999, 09, Pr8-1029-Pr8-1034.	0.2	0
39	Characterization of SiOxNy films deposited from SiCl <sub>4</sub> by remote plasma-enhanced chemical vapor deposition. Thin Solid Films, 1998, 317, 149-152.	1.8	5
40	Dielectric relaxation of amorphous and textured MIS-capacitor thin films. Solid-State Electronics, 1998, 42, 925-930.	1.4	3
41	Relationship between the microstructure and the water permeability of transparent gas barrier coatings. Surface and Coatings Technology, 1998, 100-101, 459-462.	4.8	10
42	Plasma assisted chemical vapor deposition silicon oxynitride films grown from SiH <sub>4</sub> +NH <sub>3</sub> +O <sub>2</sub> gas mixtures. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1998, 16, 2757-2761.	2.1	9
43	X-ray absorption spectroscopy and atomic force microscopy study of bias-enhanced nucleation of diamond films. Applied Physics Letters, 1998, 72, 2105-2107.	3.3	41
44	Influence of oxygen on the nucleation and growth of diamond films. Thin Solid Films, 1997, 303, 34-38.	1.8	5
45	Effect of surface fractality on the permeability of transparent gas barrier coatings. Advanced Materials, 1997, 9, 654-658.	21.0	20
46	Dielectric and Raman spectroscopy of MWCVD diamond thin films. Journal of Materials Science: Materials in Electronics, 1996, 7, 297.	2.2	9
47	Influence of Methane Concentration on the Nucleation and Growth Stages in Diamond Film Deposition. Physica Status Solidi A, 1996, 154, 23-32.	1.7	12
48	SiOxNy films deposited by remote plasma enhanced chemical vapor deposition using SiCl <sub>4</sub> . Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1996, 14, 2088-2093.	2.1	17
49	CVD of Covalent Compounds and high-T <sub>c</sub> superconductors. Advanced Materials, 1995, 7, 111-119.	21.0	4
50	Deposition of diamond and boron nitride films by plasma chemical vapour deposition. Surface and Coatings Technology, 1995, 70, 163-174.	4.8	11
51	Influence of oxygen on the deposition of diamond coatings by microwave plasma CVD. Vacuum, 1994, 45, 1015-1016.	3.5	5
52	STM nanometric study of the initial stages of diamond film growth: quantitative measurement of {111} and {100} surface roughness. Diamond and Related Materials, 1994, 3, 715-719.	3.9	5
53	Study of the plasma discharges in diamond deposition with different O <sub>2</sub> concentrations. Diamond and Related Materials, 1994, 3, 1183-1187.	3.9	12
54	Nucleation and initial stages of growth of diamond films on silicon. Scripta Metallurgica Et Materialia, 1994, 31, 1103-1108.	1.0	1

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55	Protective Coatings for Optical Systems. , 1994, , 523-551.		0
56	Micromechanical properties of diamond films deposited by microwave-plasma-enhanced chemical vapour deposition. Diamond and Related Materials, 1993, 2, 933-938.	3.9	9
57	Optical emission characterization of CH <sub>4</sub> +H <sub>2</sub> discharges for diamond deposition. Journal of Applied Physics, 1993, 74, 3752-3757.	2.5	46
58	Influence of the discharge frequency (35 kHz and 13.56 MHz) on the composition of plasma enhanced chemical vapor deposition aC:H films. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1993, 11, 143-146.	2.1	12
59	Plasma-enhanced chemically vapour deposited Si <sub>3</sub> N <sub>4</sub> thin films for optical waveguides. Thin Solid Films, 1992, 220, 311-314.	1.8	11
60	Silicon nitride films deposited from SiF <sub>4</sub> /NH <sub>3</sub> gas mixtures. Journal of Materials Science, 1991, 26, 4683-4686.	3.7	3
61	I.r. spectra resolution in fluorinated silicon nitride films. Journal of Materials Science, 1991, 26, 6244-6248.	3.7	1
62	Infrared absorption and x-ray photoelectron spectroscopy studies of the anodic oxidation of plasma silicon nitride. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1991, 9, 2285-2288.	2.1	0
63	Oxynitride layers obtained by anodic oxidation of plasma-enhanced chemically vapour deposited Si <sub>3</sub> N <sub>4</sub> films. Thin Solid Films, 1989, 175, 49-53.	1.8	2
64	Influence on the electrical characteristics of the -NH radicals incorporated into PECVD silicon nitride films. Vacuum, 1989, 39, 727-729.	3.5	12
65	Theoretical Approach for the Constant Voltage Stage in Anodic Oxidation. Journal of the Electrochemical Society, 1986, 133, 876-879.	2.9	19